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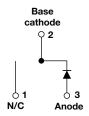
Vishay Semiconductors

HALOGEN

FREE

# HEXFRED®, Ultrafast Soft Recovery Diode, 8 A





PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub> 8 A					
$V_{R}$	1200 V				
V <sub>F</sub> at I <sub>F</sub>	2.4 V				
t <sub>rr</sub> (typ.)	28 ns				
T <sub>J</sub> max.	150 °C				
Package	D <sup>2</sup> PAK (TO-263AB)				
Circuit configuration	Single				

#### **FEATURES**

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **BENEFITS**

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

#### **DESCRIPTION**

VS-HFA08TB120S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A continuous current, the VS-HFA08TB120S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>RRM</sub>) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TB120S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V <sub>R</sub>		1200	V		
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	8			
Single pulse forward current	I <sub>FSM</sub>		130	Α		
Maximum repetitive forward current	I <sub>FRM</sub>		32			
Maximum naviar dissination	-	T <sub>C</sub> = 25 °C	73.5	10/		
Maximum power dissipation	P <sub>D</sub>	T <sub>C</sub> = 100 °C	29	W		
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C		

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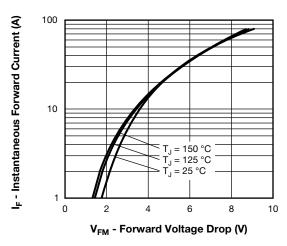
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<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V <sub>BR</sub>	Ι <sub>R</sub> = 100 μΑ	1200	-	-		
		I <sub>F</sub> = 8.0 A	-	2.6	3.3	V	
Maximum forward voltage	V <sub>FM</sub>	I <sub>F</sub> = 16 A	-	3.4	4.3		
		I <sub>F</sub> = 8.0 A, T <sub>J</sub> = 125 °C	-	2.4	3.1		
Maximum reverse	,	$V_R = V_R$ rated	-	0.31	10		
leakage current	I <sub>RM</sub>	$T_J = 125 ^{\circ}\text{C}, V_R = 0.8 \times V_R \text{ rated}$	-	135	1000	μA	
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	-	11	20	pF	
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH	

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	A/μs, V <sub>R</sub> = 30 V	-	28	-	ns	
Reverse recovery time	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	63	95		
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C	$I_F = 8.0 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	106	160		
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	4.5	8.0	А	
reak recovery current	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	6.2	11		
Povorno rocoveni chargo	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	140	380	nC	
Reverse recovery charge	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	335	880	IIC	
Peak rate of fall of recovery current during t <sub>b</sub>	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	133	-	A/µs	
	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	85	-		

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C		
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	1.7	K/W		
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	40	NVV		
Weight			-	2.0	-	g		
vveignt			-	0.07	-	OZ.		
Marking device		Case style D <sup>2</sup> PAK (TO-263AB)		HFA08	ΓB120S			

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1000 T<sub>J</sub> = 150 °C T<sub>J</sub> = 150 °C T<sub>J</sub> = 100 °C T<sub>J</sub> = 100 °C T<sub>J</sub> = 100 °C T<sub>J</sub> = 25 °C T<sub>J</sub> = 25 °C T<sub>J</sub> = 25 °C T<sub>J</sub> = 25 °C T<sub>J</sub> = 100 °C T<sub>J</sub> = 25 °C T<sub>J</sub> = 100 °C T<sub></sub>

Fig. 1 - Maximum Forward Voltage Drop Characteristics

Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

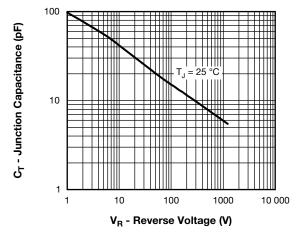


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

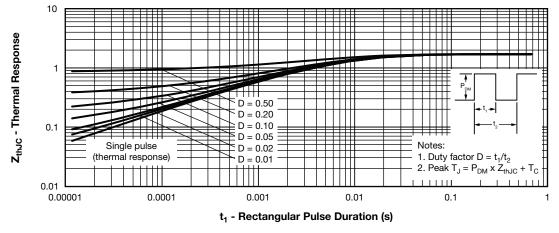


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

**I**r. (A)

100

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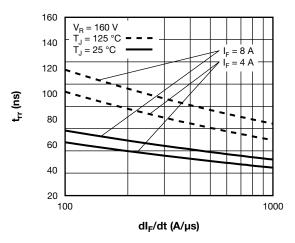
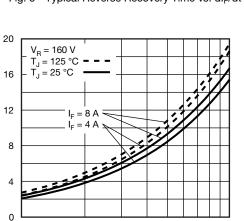


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt



 $\label{eq:dlf} dl_{\text{F}}/dt \, \text{(A/$\mu$s)}$  Fig. 6 - Typical Recovery Current vs.  $dl_{\text{F}}/dt$ 

1000

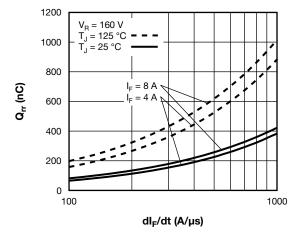


Fig. 7 - Typical Stored Charge vs.  $dI_F/dt$  (Per Leg)

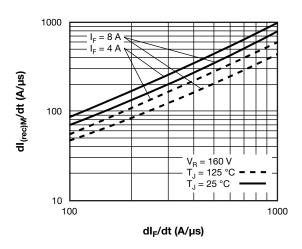
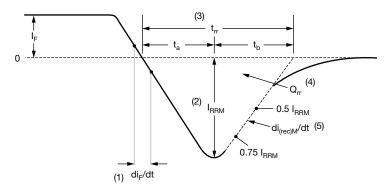


Fig. 8 - Typical dl<sub>(rec)M</sub>/dt vs. dl<sub>F</sub>/dt

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- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$

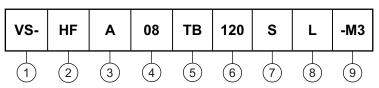
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 9 - Reverse Recovery Waveform and Definitions

#### **ORDERING INFORMATION TABLE**

**Device code** 



- 1 Vishay Semiconductors product
- 2 HEXFRED® family
- Process designator: A = electron irradiated
- 4 Current rating (08 = 8 A)
- 5 Package outline (TB = TO-220, 2 leads)
- Voltage rating (120 = 1200 V)
- 7  $S = D^2PAK (TO-263AB)$
- 8 • None = tube (50 pieces)
  - L = tape and reel (left oriented)
  - R = tape and reel (right oriented)
- 9 Environmental digit:
  - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free



## VS-HFA08TB120S-M3

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ORDERING INFORMATION (Example)						
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-HFA08TB120S-M3	50	Antistatic plastic tube				
VS-HFA08TB120SR-M3	800	13" diameter reel				
VS-HFA08TB120SL-M3	800	13" diameter reel				

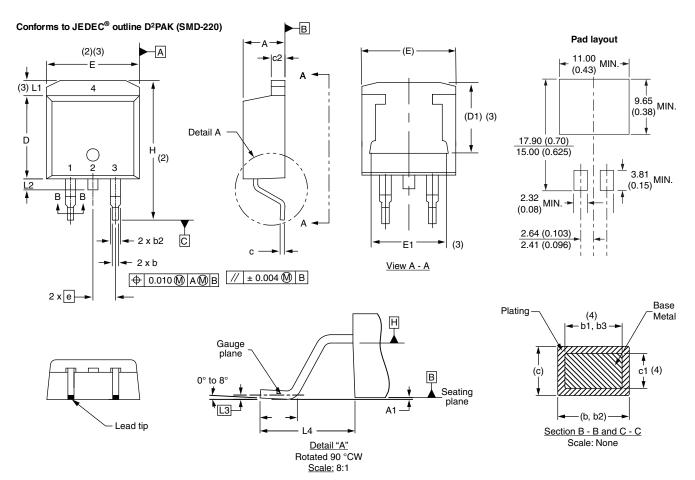
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?96164			
Part marking information	www.vishay.com/doc?95444			
Packaging information	www.vishay.com/doc?96424			



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## D<sup>2</sup>PAK

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIM	MILLIMETERS		INCHES	
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STWBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010	BSC	
L4	4.78	5.28	0.188	0.208	

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

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